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January 2014

# FDD1600N10ALZ

# N-Channel PowerTrench® MOSFET 100 V, 6.8 A, 160 m $\Omega$

#### **Features**

- $R_{DS(on)}$  = 124 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 3.4 A
- $R_{DS(on)} = 175 \text{ m}\Omega \text{ (Typ.)} @ V_{GS} = 5 \text{ V, } I_D = 2.1 \text{ A}$
- Low Gate Charge (Typ.2.78 nC)
- Low C<sub>rss</sub> (Typ. 2.04 pF)
- · Fast Switching
- · 100% Avalanche Tested
- · Improved dv/dt Capability
- · RoHS Compliant

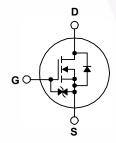
# **Description**

This N-Channel MOSFET is produced using Fairchld Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance and maintain superior switching performance.

### **Application**

- · Consumer Appliances
- · LED TV and Monitor
- · Synchronous Rectification
- Uninterruptible Power Supply
- · Micro Solar Inverter





### **MOSFET Maximum Ratings** T<sub>C</sub> = 25°C unless otherwise noted.

Symbol			FDD1600N10ALZ	Unit		
V <sub>DSS</sub>	Drain to Source Voltage			100	V	
V <sub>GSS</sub>	Gate to Source Voltage			±20	V	
	Drain Current	- Continuous (T <sub>C</sub> = 25°C)		6.8		
ID	Drain Current	- Continuous (T <sub>C</sub> = 100°C)		4.3	_ A	
I <sub>DM</sub>	Drain Current	Drain Current - Pulsed (Note		13.6	Α	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)			5.08	mJ	
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	6.0	V/ns	
D	Dower Dissinction	(T <sub>C</sub> = 25°C)		14.9	W	
$P_{D}$	Power Dissipation  - Derate Above 25°C		0.12	W/°C		
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C	
T <sub>L</sub>	Maximum Lead Temperatur	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			°C	

#### **Thermal Characteristics**

Symbol	Parameter	FDD1600N10ALZ	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	8.4	°C/W
R <sub>0,IA</sub>	Thermal Resistance, Junction to Ambient, Max.	87	30/00

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDD1600N10ALZ	1600N10ALZ	DPAK	Tape and Reel	330 mm	16 mm	2500 units

# **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter Test Conditions		Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	100	-	-	V
ΔBV <sub>DSS</sub> / ΔΤ <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C	-	0.1	-	V/°C
1	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V	-	-	1	μА
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	500	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V	-	-	±10	μΑ

#### **On Characteristics**

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	1.4	-	2.8	V
P	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 3.4 \text{ A}$	-	124	160	mΩ
R <sub>DS(on)</sub>	on) Static Drain to Source On Resistance	V <sub>GS</sub> = 5 V, I <sub>D</sub> = 2.1 A	-	175	375	1115.2
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 6.8 A	-	19.6	-	S

#### **Dynamic Characteristics**

-							
C <sub>iss</sub>	Input Capacitance	\/ - F0\/\\	V 50.V.V 0.V		169	225	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 50 \text{ V}, V_{GS}$ = f = 1 MHz	<sub>S</sub> = 0 V,	-\	43	55	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 1011 12		- \	2.04	-	pF
C <sub>oss(er)</sub>	Energy Related Output Capacitance	$V_{DS}$ = 50 V, $V_{GS}$	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V		85	-	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V	V <sub>GS</sub> = 10 V	V <sub>DD</sub> = 50 V,	-	2.78	3.61	nC
Q <sub>g(tot)</sub>	Total Gate Charge at 5V	V <sub>GS</sub> = 5 V	I <sub>D</sub> = 6.8 A		1.5	1.95	nC
$Q_{gs}$	Gate to Source Gate Charge			-	0.72	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge			-	0.56	-	nC
V <sub>plateau</sub>	Gate Plateau Volatge		(Note 4)	-	4.02	-	V
Q <sub>sync</sub>	Total Gate Charge Sync.	$V_{DS} = 0 \text{ V}, I_{D} = 3$	3.4 A	- /	2.5	-	nC
Q <sub>oss</sub>	Output Charge	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V		- /	5.2	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz		-/	2.1	-	Ω

#### **Switching Characteristics**

_							
t <sub>d(on)</sub>	Turn-On Delay Time			-	7	24	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 50 \text{ V}, I_{D} = 6.8 \text{ A},$		-	2	14	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS}$ = 10 V, $R_{G}$ = 4.7 $\Omega$		-	13	36	ns
t <sub>f</sub>	Turn-Off Fall Time		(Note 4)	-	2	14	ns

#### **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	6.8	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	13.6	Α
$V_{SD}$	Drain to Source Diode Forward Voltage $V_{GS} = 0 \text{ V}, I_{SD} = 6.$	.8 A -	-	1.3	V
t <sub>rr</sub>	Reverse Recovery Time $V_{GS} = 0 \text{ V}, I_{SD} = 6.$	.8 A, V <sub>DS</sub> = 50 V, -	37	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge $dI_F/dt = 100 A/\mu s$	-	42	-	nC

#### Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 1 mH,  $I_{AS}$  =3.18 A,  $R_G$  = 25  $\Omega$ , starting  $T_J$  = 25°C.
- 3. I  $_{SD} \leq$  6.8 A, di/dt  $\leq$  200 A/µs, V  $_{DD} \leq$  BV  $_{DSS},$  starting T  $_{J}$  = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

# **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

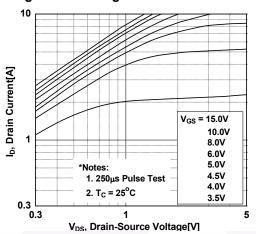


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

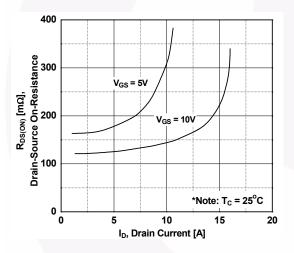
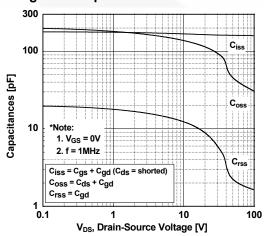


Figure 5. Capacitance Characteristics



**Figure 2. Transfer Characteristics** 

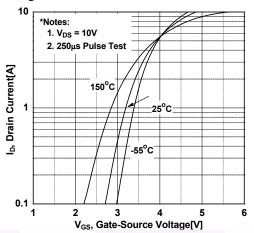


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

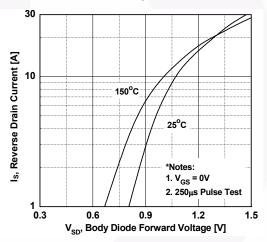
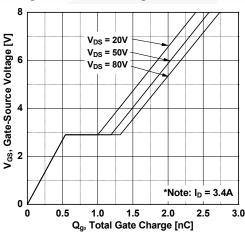


Figure 6. Gate Charge Characteristics



### **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

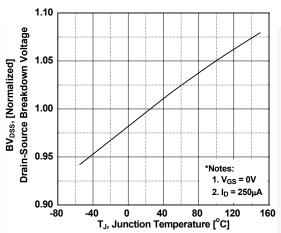


Figure 9. Maximum Safe Operating Area

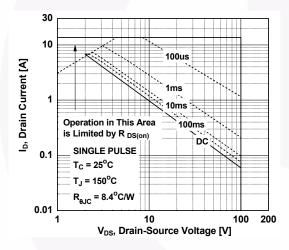


Figure 11. Eoss vs. Drain to Source Voltage

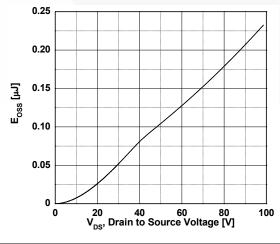


Figure 8. On-Resistance Variation vs. Temperature

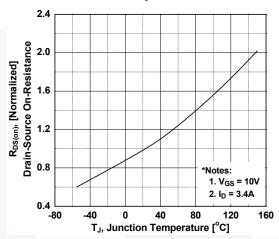


Figure 10. Maximum Drain Current vs. Case Temperature

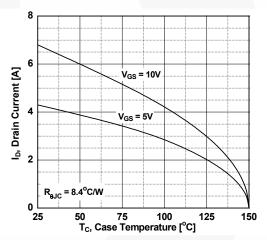
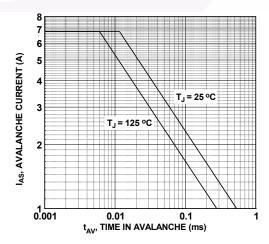
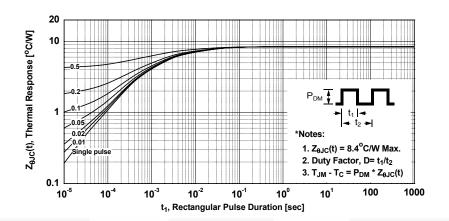


Figure 12. Unclamped Inductive Switching Capability



# **Typical Performance Characteristics** (Continued)

Figure 13. Transient Thermal Response Curve



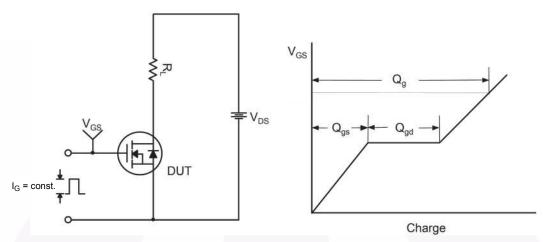


Figure 14. Gate Charge Test Circuit & Waveform

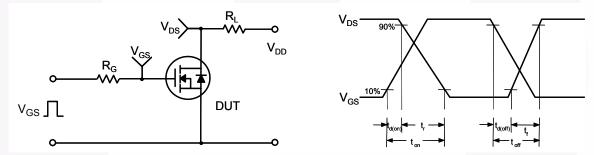


Figure 15. Resistive Switching Test Circuit & Waveforms

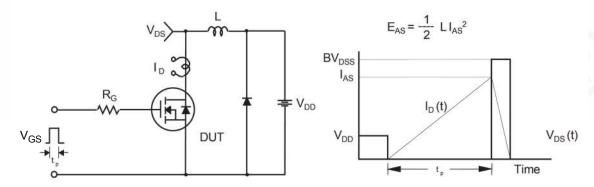


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

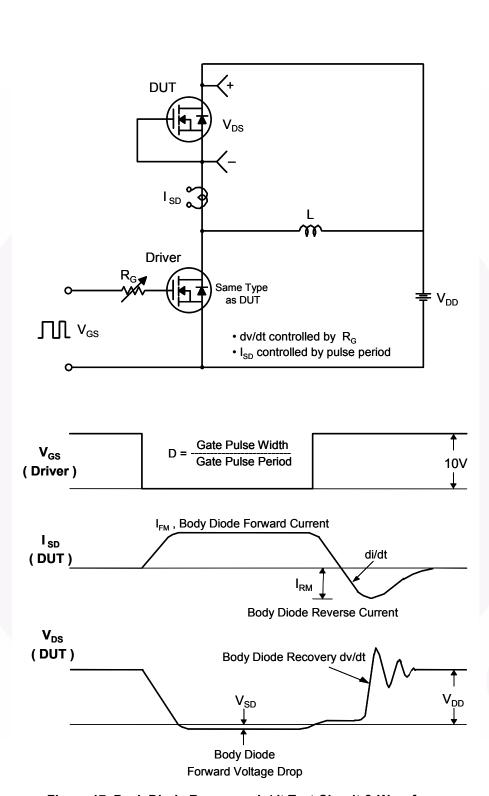


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

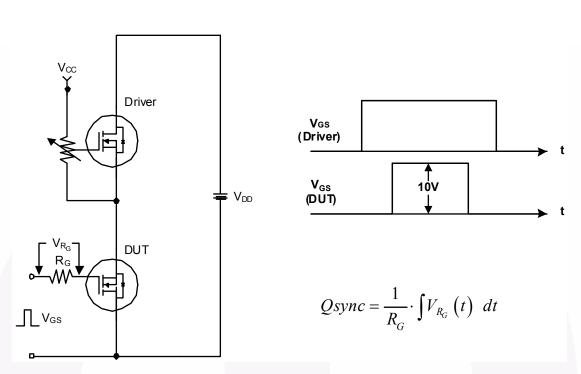


Figure 18. Total Gate Charge Qsync. Test Circuit & Waveforms

#### **Mechanical Dimensions** -5.55 MIN-1.27 6.22 5.97 6.50 MIN 1.02 MAX C 2 (0.59)0.89 2.29 2.28 0.25\ A\ C 4.57 LAND PATTERN RECOMMENDATION 2.39 SFF 2.18 4.32 MIN NOTE D 0.58 0.45 5.21 MIN 10.41 9.40 SFF DFTAIL A ○ 0.10 B 0.51 GAGE PLANE NOTES: UNLESS OTHERWISE SPECIFIED THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA. ALL DIMENSIONS ARE IN MILLIMETERS. 10 (1.54)DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009. SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION. PRESENCE OF TRIMMED CENTER LEAD .78 0.127 MAX IS OPTIONAL. DIMENSIONS ARE EXCLUSSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS. SEATING PLANE

Figure 19. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

(2.90)

DETAIL

(ROTATED -90°) SCALE: 12X

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LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD

DRAWING NUMBER AND REVISION: MKT-T0252A03REV9.

TO228P991X239-3N

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